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Understanding <u>Embedded - FPGAs (Field</u> <u>Programmable Gate Array)</u>

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details

Product Status	Obsolete
Number of LABs/CLBs	-
Number of Logic Elements/Cells	-
Total RAM Bits	110592
Number of I/O	154
Number of Gates	600000
Voltage - Supply	1.14V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	208-BFQFP
Supplier Device Package	208-PQFP (28x28)
Purchase URL	https://www.e-xfl.com/product-detail/microsemi/a3p600l-1pqg208i

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

Flash*Freeze Technology and Low Power Modes



Figure 2-11 • FSM State Diagram

Global Resources in Low Power Flash Devices

Step 1

Run Synthesis with default options. The Synplicity log shows the following device utilization:

Cell usage:

	cell count	area	count*area
DFN1E1C1	1536	2.0	3072.0
BUFF	278	1.0	278.0
INBUF	10	0.0	0.0
VCC	9	0.0	0.0
GND	9	0.0	0.0
OUTBUF	6	0.0	0.0
CLKBUF	3	0.0	0.0
PLL	2	0.0	0.0
TOTAL	1853		3350.0

Step 2

Run Compile with the **Promote regular nets whose fanout is greater than** option selected in Designer; you will see the following in the Compile report:

Device	utilizatic	on rep	port:					
=======			==== 9 • 1 5	26	Total·	12024	(11 119)	
TO (W/		Used	1. TO	10	Total	1/7	(12,02%)	
IU (W/	CIUCKS)	Usec	1.	19	IOLAI.	147	(12.93%)	
Differe	ntial 10	Used	1.	0	Total:	05	(0.00%)	
GLOBAL		Used	1.	8	Total:	18	(44.44%)	
РББ		Used	1:	2	Total:	2	(100.00%)	
RAM/FIF	0	Used	1:	0	Total:	24	(0.00%)	
FlashRO	М	Used	1:	0	Total:	1	(0.00%)	
The fol	 lowing net	s hav	ze been	as	ssigned	to a glo	bal resourd	ce:
Fanout	Туре		Name					
 1536	INT_NET		Net	: 1	EN_ALL_C			
	_		Driver	: E	EN_ALL_p	ad_CLKIN	Т	
			Source	: 7	AUTO PRO	MOTED		
1536	SET/RESEI	NET	Net	: 7	ACLR C			
		_	Driver	: 7	ACLR pad	CLKINT		
			Source	: 7	AUTO PRO	MOTED		
256	CLK NET		Net	: (OCLK1 c			
	_		Driver	: (OCLK1 pa	d CLKINT		
			Source	: 7	AUTO PRO	- MOTED		
256	CLK NET		Net	: (OCLK2 c			
	—		Driver	: (CLK2 pa	d CLKINT	1	
			Source	: 7	AUTO PRO	- MOTED		
256	CLK NET		Net	: (OCLK3 c			
	—		Driver	: (CLK3 pa	d CLKINT	1	
			Source	: 7	AUTO PRO	- MOTED		
256	CLK NET		Net	: :	31N14			
	_		Driver	: :	1I5/Cor	е		
			Source	: E	ESSENTIA	L		
256	CLK NET		Net	: :	\$1N12			
	—		Driver	: :	51I6/Cor	e		
			Source	: E	ESSENTIA	L		
256	CLK_NET		Net	: :	\$1N10			
	—		Driver	: :	31I6/Cor	е		
			Source	: F	SSENTIA	L		

Designer will promote five more signals to global due to high fanout. There are eight signals assigned to global networks.

Clock Conditioning Circuits in Low Power Flash Devices and Mixed Signal FPGAs

Device-Specific Layout

Two kinds of CCCs are offered in low power flash devices: CCCs with integrated PLLs, and CCCs without integrated PLLs (simplified CCCs). Table 4-5 lists the number of CCCs in various devices.

Table 4-5 • Number	of CCCs b	y Device Size and	Package

Device			CCCs with	CCCs without	
ProASIC3	IGLOO	Package	PLLs	(simplified CCC)	
A3PN010	AGLN010	All	0	2	
A3PN015	AGLN015	All	0	2	
A3PN020	AGLN020	All	0	2	
	AGLN060	CS81	0	6	
A3PN060	AGLN060	All other packages	1	5	
	AGLN125	CS81	0	6	
A3PN125	AGLN125	All other packages	1	5	
	AGLN250	CS81	0	6	
A3PN250	AGLN250	All other packages	1	5	
A3P015	AGL015	All	0	2	
A3P030	AGL030/AGLP030	All	0	2	
	AGL060/AGLP060	CS121/CS201	0	6	
A3P060	AGL060/AGLP060	All other packages	1	5	
A3P125	AGL125/AGLP125	All	1	5	
A3P250/L	AGL250	All	1	5	
A3P400	AGL400	All	1	5	
A3P600/L	AGL600	All	1	5	
A3P1000/L	AGL1000	All	1	5	
A3PE600	AGLE600	PQ208	2	4	
A3PE600/L		All other packages	6	0	
A3PE1500		PQ208	2	4	
A3PE1500		All other packages	6	0	
A3PE3000/L		PQ208	2	4	
A3PE3000/L	AGLE3000	All other packages	6	0	
Fusion Devices		· · · ·			
AFS090		All	1	5	
AFS250, M1AFS250)	All	1	5	
AFS600, M7AFS600	0, M1AFS600	All	2	4	
AFS1500, M1AFS1500		All	2	4	

Note: nano 10 k, 15 k, and 20 k offer 6 global MUXes instead of CCCs.



Clock Conditioning Circuits in Low Power Flash Devices and Mixed Signal FPGAs

External Feedback Configuration

For certain applications, such as those requiring generation of PCB clocks that must be matched with existing board delays, it is useful to implement an external feedback, EXTFB. The Phase Detector of the PLL core will receive CLKA and EXTFB as inputs. EXTFB may be processed by the fixed System Delay element as well as the *M* divider element. The EXTFB option is currently not supported.

After setting all the required parameters, users can generate one or more PLL configurations with HDL or EDIF descriptions by clicking the **Generate** button. SmartGen gives the option of saving session results and messages in a log file:

Name	:	test_pll
Family	:	ProASIC3E
Output Format	:	VHDL
Туре	:	Static PLL
Input Freq(MHz)	:	10.000
CLKA Source	:	Hardwired I/O
Feedback Delay Value Index	:	1
Feedback Mux Select	:	2
XDLY Mux Select	:	No
Primary Freq(MHz)	:	33.000
Primary PhaseShift	:	0
Primary Delay Value Index	:	1
Primary Mux Select	:	4
Secondarv1 Freg(MHz)	:	66.000
Use GLB	:	YES
Use YB	:	YES
GLB Delay Value Index	:	1
YB Delay Value Index	:	1
Secondaryl DhaseShift		0
Secondary1 Mux Select		4
Secondary? Freq(MHz)	:	101 000
		VES
	:	NO
GLC Delay Value Index	:	1
VC Dolow Volue Index	:	1
Cocondomy? Descellift	:	1
Secondary2 Mux Soloat	:	0
Secondaryz Mux Serect	•	7
Primary Clock frequency 55.555		
Primary Clock Phase Shill 0.000	~	
Primary Clock Output Delay from	Ċ.	LKA 0.180
Secondary Clock Frequency 66.66) /) (0
Secondaryl Clock Phase Shift 0.0	00	
Secondaryl Clock Global Output I	Je.	Lay from CLKA 0.180
Secondaryi Clock Core Output Del	La	y Irom CLKA 0.625
Cogondomy) (logi-freemen - 100 (20	0
Secondaryz Clock Irequency 100.0	10	0
Secondary2 CLOCK Phase Shift 0.0	10	
Secondaryz Clock Global Output I	Je	TAY ITOM CLKA U.180

Below is an example Verilog HDL description of a legal PLL core configuration generated by SmartGen:

module test_pll(POWERDOWN,CLKA,LOCK,GLA); input POWERDOWN, CLKA; output LOCK,GLA;



Clock Conditioning Circuits in Low Power Flash Devices and Mixed Signal FPGAs

Primary Clock Output Delay from CLKA -3.020 Secondary1 Clock frequency 40.000 Secondary1 Clock Phase Shift 0.000 Secondary1 Clock Global Output Delay from CLKA 2.515

Next, perform simulation in Model*Sim* to verify the correct delays. Figure 4-30 shows the simulation results. The delay values match those reported in the SmartGen PLL Wizard.



Figure 4-30 • Model Sim Simulation Results

The timing can also be analyzed using SmartTime in Designer. The user should import the synthesized netlist to Designer, perform Compile and Layout, and then invoke SmartTime. Go to **Tools** > **Options** and change the maximum delay operating conditions to **Typical Case**. Then expand the Clock-to-Out paths of GLA and GLB and the individual components of the path delays are shown. The path of GLA is shown in Figure 4-31 on page 123 displaying the same delay value.

FlashROM in Microsemi's Low Power Flash Devices

SmartGen allows you to generate the FlashROM netlist in VHDL, Verilog, or EDIF format. After the FlashROM netlist is generated, the core can be instantiated in the main design like other SmartGen cores. Note that the macro library name for FlashROM is UFROM. The following is a sample FlashROM VHDL netlist that can be instantiated in the main design:

```
library ieee;
use ieee.std_logic_1164.all;
library fusion;
entity FROM_a is
  port( ADDR : in std_logic_vector(6 downto 0); DOUT : out std_logic_vector(7 downto 0));
end FROM a;
architecture DEF_ARCH of FROM_a is
  component UFROM
    generic (MEMORYFILE:string);
    port(D00, D01, D02, D03, D04, D05, D06, D07 : out std_logic;
      ADDR0, ADDR1, ADDR2, ADDR3, ADDR4, ADDR5, ADDR6 : in std_logic := 'U') ;
  end component;
  component GND
    port( Y : out std_logic);
  end component;
signal U_7_PIN2 : std_logic ;
begin
  GND_1_net : GND port map(Y => U_7_PIN2);
  UFROM0 : UFROM
  generic map(MEMORYFILE => "FROM_a.mem")
  port map(DOO => DOUT(0), DO1 => DOUT(1), DO2 => DOUT(2), DO3 => DOUT(3), DO4 => DOUT(4),
    DO5 => DOUT(5), DO6 => DOUT(6), DO7 => DOUT(7), ADDR0 => ADDR(0), ADDR1 => ADDR(1),
    ADDR2 => ADDR(2), ADDR3 => ADDR(3), ADDR4 => ADDR(4), ADDR5 => ADDR(5),
    ADDR6 => ADDR(6));
```

end DEF_ARCH;

SmartGen generates the following files along with the netlist. These are located in the SmartGen folder for the Libero SoC project.

- 1. MEM (Memory Initialization) file
- 2. UFC (User Flash Configuration) file
- 3. Log file

The MEM file is used for simulation, as explained in the "Simulation of FlashROM Design" section on page 143. The UFC file, generated by SmartGen, has the FlashROM configuration for single or multiple devices and is used during STAPL generation. It contains the region properties and simulation values. Note that any changes in the MEM file will not be reflected in the UFC file. Do not modify the UFC to change FlashROM content. Instead, use the SmartGen GUI to modify the FlashROM content. See the "Programming File Generation for FlashROM Design" section on page 143 for a description of how the UFC file is used during the programming file generation. The log file has information regarding the file type and file location.

SRAM and FIFO Memories in Microsemi's Low Power Flash Devices

Initializing the RAM/FIFO

The SRAM blocks can be initialized with data to use as a lookup table (LUT). Data initialization can be accomplished either by loading the data through the design logic or through the UJTAG interface. The UJTAG macro is used to allow access from the JTAG port to the internal logic in the device. By sending the appropriate initialization string to the JTAG Test Access Port (TAP) Controller, the designer can put the JTAG circuitry into a mode that allows the user to shift data into the array logic through the JTAG port using the UJTAG macro. For a more detailed explanation of the UJTAG macro, refer to the "FlashROM in Microsemi's Low Power Flash Devices" section on page 133.

A user interface is required to receive the user command, initialization data, and clock from the UJTAG macro. The interface must synchronize and load the data into the correct RAM block of the design. The main outputs of the user interface block are the following:

- Memory block chip select: Selects a memory block for initialization. The chip selects signals for each memory block that can be generated from different user-defined pockets or simple logic, such as a ring counter (see below).
- Memory block write address: Identifies the address of the memory cell that needs to be initialized.
- Memory block write data: The interface block receives the data serially from the UTDI port of the UJTAG macro and loads it in parallel into the write data ports of the memory blocks.
- Memory block write clock: Drives the WCLK of the memory block and synchronizes the write data, write address, and chip select signals.

Figure 6-8 shows the user interface between UJTAG and the memory blocks.



Figure 6-8 • Interfacing TAP Ports and SRAM Blocks

An important component of the interface between the UJTAG macro and the RAM blocks is a serialin/parallel-out shift register. The width of the shift register should equal the data width of the RAM blocks. The RAM data arrives serially from the UTDI output of the UJTAG macro. The data must be shifted into a shift register clocked by the JTAG clock (provided at the UDRCK output of the UJTAG macro).

Then, after the shift register is fully loaded, the data must be transferred to the write data port of the RAM block. To synchronize the loading of the write data with the write address and write clock, the output of the shift register can be pipelined before driving the RAM block.

The write address can be generated in different ways. It can be imported through the TAP using a different instruction opcode and another shift register, or generated internally using a simple counter. Using a counter to generate the address bits and sweep through the address range of the RAM blocks is

SRAM and FIFO Memories in Microsemi's Low Power Flash Devices

Example of RAM Initialization

This section of the document presents a sample design in which a 4×4 RAM block is being initialized through the JTAG port. A test feature has been implemented in the design to read back the contents of the RAM after initialization to verify the procedure.

The interface block of this example performs two major functions: initialization of the RAM block and running a test procedure to read back the contents. The clock output of the interface is either the write clock (for initialization) or the read clock (for reading back the contents). The Verilog code for the interface block is included in the "Sample Verilog Code" section on page 167.

For simulation purposes, users can declare the input ports of the UJTAG macro for easier assignment in the testbench. However, the UJTAG input ports should not be declared on the top level during synthesis. If the input ports of the UJTAG are declared during synthesis, the synthesis tool will instantiate input buffers on these ports. The input buffers on the ports will cause Compile to fail in Designer.

Figure 6-10 shows the simulation results for the initialization step of the example design.

The CLK_OUT signal, which is the clock output of the interface block, is the inverted DR_UPDATE output of the UJTAG macro. It is clear that it gives sufficient time (while the TAP Controller is in the Data Register Update state) for the write address and data to become stable before loading them into the RAM block.

Figure 6-11 presents the test procedure of the example. The data read back from the memory block matches the written data, thus verifying the design functionality.

Figure 6-10 • Simulation of Initialization Step

Figure 6-11 • Simulation of the Test Procedure of the Example

SRAM and FIFO Memories in Microsemi's Low Power Flash Devices

Date	Changes			
v1.1 (continued)	Table 6-1 • Flash-Based FPGAs and associated text were updated to include the IGLOO PLUS family. The "IGLOO Terminology" section and "ProASIC3 Terminology" section are new.	150		
	The text introducing Table 6-8 • Memory Availability per IGLOO and ProASIC3 Device was updated to replace "A3P030 and AGL030" with "15 k and 30 k gate devices." Table 6-8 • Memory Availability per IGLOO and ProASIC3 Device was updated to remove AGL400 and AGLE1500 and include IGLOO PLUS and ProASIC3L devices.	162		

I/O Structures in IGLOOe and ProASIC3E Devices

Low Power Flash Device I/O Support

The low power flash FPGAs listed in Table 8-1 support I/Os and the functions described in this document.

Table 8-1 • Flash-Based FPGAs

Series	Family [*]	Description
IGLOO	IGLOOe	Higher density IGLOO FPGAs with six PLLs and additional I/O standards
ProASIC3	ProASIC3E	Higher density ProASIC3 FPGAs with six PLLs and additional I/O standards
	ProASIC3L	ProASIC3 FPGAs supporting 1.2 V to 1.5 V with Flash*Freeze technology
	Military ProASIC3/EL	Military temperature A3PE600L, A3P1000, and A3PE3000L
	RT ProASIC3	Radiation-tolerant RT3PE600L and RT3PE3000L

Note: *The device names link to the appropriate datasheet, including product brief, DC and switching characteristics, and packaging information.

IGLOO Terminology

In documentation, the terms IGLOO series and IGLOO devices refer to all of the IGLOO devices as listed in Table 8-1. Where the information applies to only one product line or limited devices, these exclusions will be explicitly stated.

ProASIC3 Terminology

In documentation, the terms ProASIC3 series and ProASIC3 devices refer to all of the ProASIC3 devices as listed in Table 8-1. Where the information applies to only one product line or limited devices, these exclusions will be explicitly stated.

To further understand the differences between the IGLOO and ProASIC3 devices, refer to the *Industry's Lowest Power FPGAs Portfolio.*

I/O Software Control in Low Power Flash Devices

Implementing I/Os in Microsemi Software

Microsemi Libero SoC software is integrated with design entry tools such as the SmartGen macro builder, the ViewDraw schematic entry tool, and an HDL editor. It is also integrated with the synthesis and Designer tools. In this section, all necessary steps to implement the I/Os are discussed.

Design Entry

There are three ways to implement I/Os in a design:

- 1. Use the SmartGen macro builder to configure I/Os by generating specific I/O library macros and then instantiating them in top-level code. This is especially useful when creating I/O bus structures.
- 2. Use an I/O buffer cell in a schematic design.
- 3. Manually instantiate specific I/O macros in the top-level code.

If technology-specific macros, such as INBUF_LVCMOS33 and OUTBUF_PCI, are used in the HDL code or schematic, the user will not be able to change the I/O standard later on in Designer. If generic I/O macros are used, such as INBUF, OUTBUF, TRIBUF, CLKBUF, and BIBUF, the user can change the I/O standard using the Designer I/O Attribute Editor tool.

Using SmartGen for I/O Configuration

The SmartGen tool in Libero SoC provides a GUI-based method of configuring the I/O attributes. The user can select certain I/O attributes while configuring the I/O macro in SmartGen. The steps to configure an I/O macro with specific I/O attributes are as follows:

- 1. Open Libero SoC.
- 2. On the left-hand side of the Catalog View, select I/O, as shown in Figure 9-2.

Figure 9-2 • SmartGen Catalog

I/O Software Control in Low Power Flash Devices

Output Buffers

There are two variations: Regular and Special.

If the **Regular** variation is selected, only the Width (1 to 128) needs to be entered. The default value for Width is 1.

The Special variation has Width, Technology, Output Drive, and Slew Rate options.

Bidirectional Buffers

There are two variations: Regular and Special.

The Regular variation has Enable Polarity (Active High, Active Low) in addition to the Width option.

The **Special** variation has Width, Technology, Output Drive, Slew Rate, and Resistor Pull-Up/-Down options.

Tristate Buffers

Same as Bidirectional Buffers.

DDR

There are eight variations: DDR with Regular Input Buffers, Special Input Buffers, Regular Output Buffers, Special Output Buffers, Regular Tristate Buffers, Special Tristate Buffers, Regular Bidirectional Buffers, and Special Bidirectional Buffers.

These variations resemble the options of the previous I/O macro. For example, the Special Input Buffers variation has Width, Technology, Voltage Level, and Resistor Pull-Up/-Down options. DDR is not available on IGLOO PLUS devices.

- 4. Once the desired configuration is selected, click the **Generate** button. The Generate Core window opens (Figure 9-4).
- 5. Enter a name for the macro. Click **OK**. The core will be generated and saved to the appropriate location within the project files (Figure 9-5 on page 257).

Figure 9-4 • Generate Core Window

6. Instantiate the I/O macro in the top-level code.

The user must instantiate the DDR_REG or DDR_OUT macro in the design. Use SmartGen to generate both these macros and then instantiate them in your top level. To combine the DDR macros with the I/O, the following rules must be met:

- The I/O standard of technology-specific I/O macros cannot be changed in the I/O Attribute Editor (see Figure 9-6).
- The user MUST instantiate differential I/O macros (LVDS/LVPECL) in the design. This is the only way to use these standards in the design (IGLOO nano and ProASIC3 nano devices do not support differential inputs).
- To implement the DDR I/O function, the user must instantiate a DDR_REG or DDR_OUT macro. This is the only way to use a DDR macro in the design.

Figure 9-6 • Assigning a Different I/O Standard to the Generic I/O Macro

Performing Place-and-Route on the Design

The netlist created by the synthesis tool should now be imported into Designer and compiled. During Compile, the user can specify the I/O placement and attributes by importing the PDC file. The user can also specify the I/O placement and attributes using ChipPlanner and the I/O Attribute Editor under MVN.

Defining I/O Assignments in the PDC File

A PDC file is a Tcl script file specifying physical constraints. This file can be imported to and exported from Designer.

Table 9-3 shows I/O assignment constraints supported in the PDC file.

Command	Action	Example	Comment				
I/O Banks Setting	/O Banks Setting Constraints						
set_iobank	Sets the I/O supply voltage, V_{CCI} , and the input reference voltage, V_{REF} , for the specified I/O bank.	<pre>set_iobank bankname [-vcci vcci_voltage] [-vref vref_voltage] set_iobank Bank7 -vcci 1.50 -vref 0.75</pre>	Must use in case of mixed I/O voltage (V _{CCI}) design				
set_vref	Assigns a V _{REF} pin to a bank.	set_vref -bank [bankname] [pinnum] set_vref -bank Bank0 685 704 723 742 761	Must use if voltage- referenced I/Os are used				
set_vref_defaults	Sets the default V_{REF} pins for the specified bank. This command is ignored if the bank does not need a V_{REF} pin.	set_vref_defaults bankname set_vref_defaults bank2					

Table 9-3 • PDC I/O Constraints

Note: Refer to the Libero SoC User's Guide for detailed rules on PDC naming and syntax conventions.

Compiling the Design

During Compile, a PDC I/O constraint file can be imported along with the netlist file. If only the netlist file is compiled, certain I/O assignments need to be completed before proceeding to Layout. All constraints that can be entered in PDC can also be entered using ChipPlanner, I/O Attribute Editor, and PinEditor.

There are certain rules that must be followed in implementing I/O register combining and the I/O DDR macro (refer to the I/O Registers section of the handbook for the device that you are using and the "DDR" section on page 256 for details). Provided these rules are met, the user can enable or disable I/O register combining by using the PDC command set_io portname -register yes |no in the I/O Attribute Editor or selecting a check box in the Compile Options dialog box (see Figure 9-7). The Compile Options dialog box appears when the design is compiled for the first time. It can also be accessed by choosing **Options** > **Compile** during successive runs. I/O register combining is off by default. The PDC command overrides the setting in the Compile Options dialog box.

Figure 9-7 • Setting Register Combining During Compile

Understanding the Compile Report

The I/O bank report is generated during Compile and displayed in the log window. This report lists the I/O assignments necessary before Layout can proceed.

When Designer is started, the I/O Bank Assigner tool is run automatically if the Layout command is executed. The I/O Bank Assigner takes care of the necessary I/O assignments. However, these assignments can also be made manually with MVN or by importing the PDC file. Refer to the "Assigning Technologies and VREF to I/O Banks" section on page 264 for further description.

The I/O bank report can also be extracted from Designer by choosing **Tools** > **Report** and setting the Report Type to **IOBank**.

This report has the following tables: I/O Function, I/O Technology, I/O Bank Resource Usage, and I/O Voltage Usage. This report is useful if the user wants to do I/O assignments manually.



I/O Software Control in Low Power Flash Devices

I/O Function

Figure 9-8 shows an example of the I/O Function table included in the I/O bank report:

Figure 9-8 • I/O Function Table

This table lists the number of input I/Os, output I/Os, bidirectional I/Os, and differential input and output I/O pairs that use I/O and DDR registers.

Note: IGLOO nano and ProASIC3 nano devices do not support differential inputs.

Certain rules must be met to implement registered and DDR I/O functions (refer to the I/O Structures section of the handbook for the device you are using and the "DDR" section on page 256).

I/O Technology

The I/O Technology table (shown in Figure 9-9) gives the values of VCCI and VREF (reference voltage) for all the I/O standards used in the design. The user should assign these voltages appropriately.

Figure 9-9 • I/O Technology Table

Figure 10-11 • DDR Input/Output Cells as Seen by ChipPlanner for IGLOO/e Devices

Verilog

module Inbuf_ddr(PAD,CLR,CLK,QR,QF);

input PAD, CLR, CLK; output QR, QF;

wire Y;

```
DDR_REG_DDR_REG_0_inst(.D(Y), .CLK(CLK), .CLR(CLR), .QR(QR), .QF(QF));
INBUF INBUF_0_inst(.PAD(PAD), .Y(Y));
```

endmodule

module Outbuf_ddr(DataR,DataF,CLR,CLK,PAD);

input DataR, DataF, CLR, CLK; output PAD;

wire Q, VCC;

```
VCC VCC_1_net(.Y(VCC));
DDR_OUT DDR_OUT_0_inst(.DR(DataR), .DF(DataF), .CLK(CLK), .CLR(CLR), .Q(Q));
OUTBUF OUTBUF_0_inst(.D(Q), .PAD(PAD));
```

endmodule

2. VCC rises to 1.5 V before programming begins.

Figure 14-3 • Programming Algorithm

The oscilloscope plot in Figure 14-3 shows a wider time interval for the programming algorithm and includes the TDI and TMS signals from the FlashPro3. These signals carry the programming information that is programmed into the device and should only start toggling after the V_{CC} core voltage reaches 1.5 V. Again, TRST from FlashPro3 and the V_{CC} core voltage of the IGLOO device are labeled. As shown in Figure 14-3, TDI and TMS are floating initially, and the core voltage is 1.2 V. When a programming command on the FlashPro3 is executed, TRST is driven HIGH and TDI is momentarily driven to ground. In response to the HIGH TRST signal, the circuit responds and pulls the core voltage to 1.5 V. After 100 ms, TRST is briefly driven LOW by the FlashPro software. This is expected behavior that ensures the device JTAG state machine is in Reset prior to programming. TRST remains HIGH for the duration of the programming. It can be seen in Figure 14-3 that the VCC core voltage signal remains at 1.5 V for approximately 50 ms before information starts passing through on TDI and TMS. This confirms that the voltage switching circuit drives the VCC core supply voltage to 1.5 V prior to programming.

Boundary Scan in Low Power Flash Devices

Microsemi's Flash Devices Support the JTAG Feature

The flash-based FPGAs listed in Table 16-1 support the JTAG feature and the functions described in this document.

Table 16-1 • Flash-Based FPGAs

Series	Family [*]	Description
IGLOO	IGLOO	Ultra-low power 1.2 V to 1.5 V FPGAs with Flash*Freeze technology
	IGLOOe	Higher density IGLOO FPGAs with six PLLs and additional I/O standards
	IGLOO nano	The industry's lowest-power, smallest-size solution
	IGLOO PLUS	IGLOO FPGAs with enhanced I/O capabilities
ProASIC3	ProASIC3	Low power, high-performance 1.5 V FPGAs
	ProASIC3E	Higher density ProASIC3 FPGAs with six PLLs and additional I/O standards
	ProASIC3 nano	Lowest-cost solution with enhanced I/O capabilities
	ProASIC3L	ProASIC3 FPGAs supporting 1.2 V to 1.5 V with Flash*Freeze technology
	RT ProASIC3	Radiation-tolerant RT3PE600L and RT3PE3000L
	Military ProASIC3/EL	Military temperature A3PE600L, A3P1000, and A3PE3000L
	Automotive ProASIC3	ProASIC3 FPGAs qualified for automotive applications
Fusion	Fusion	Mixed signal FPGA integrating ProASIC [®] 3 FPGA fabric, programmable analog block, support for ARM [®] Cortex [™] -M1 soft processors, and flash memory into a monolithic device

Note: *The device names link to the appropriate datasheet, including product brief, DC and switching characteristics, and packaging information.

IGLOO Terminology

In documentation, the terms IGLOO series and IGLOO devices refer to all of the IGLOO devices as listed in Table 16-1. Where the information applies to only one product line or limited devices, these exclusions will be explicitly stated.

ProASIC3 Terminology

In documentation, the terms ProASIC3 series and ProASIC3 devices refer to all of the ProASIC3 devices as listed in Table 16-1. Where the information applies to only one product line or limited devices, these exclusions will be explicitly stated.

To further understand the differences between the IGLOO and ProASIC3 devices, refer to the *Industry's Lowest Power FPGAs Portfolio*.

UJTAG Applications in Microsemi's Low Power Flash Devices

UJTAG Support in Flash-Based Devices

The flash-based FPGAs listed in Table 17-1 support the UJTAG feature and the functions described in this document.

Table 17-1 • Flash-Based FPGAs

Series	Family [*]	Description
IGLOO	IGLOO	Ultra-low power 1.2 V to 1.5 V FPGAs with Flash*Freeze technology
	IGLOOe	Higher density IGLOO FPGAs with six PLLs and additional I/O standards
	IGLOO nano	The industry's lowest-power, smallest-size solution
	IGLOO PLUS	IGLOO FPGAs with enhanced I/O capabilities
ProASIC3	ProASIC3	Low power, high-performance 1.5 V FPGAs
	ProASIC3E	Higher density ProASIC3 FPGAs with six PLLs and additional I/O standards
	ProASIC3 nano	Lowest-cost solution with enhanced I/O capabilities
	ProASIC3L	ProASIC3 FPGAs supporting 1.2 V to 1.5 V with Flash*Freeze technology
	RT ProASIC3	Radiation-tolerant RT3PE600L and RT3PE3000L
	Military ProASIC3/EL	Military temperature A3PE600L, A3P1000, and A3PE3000L
	Automotive ProASIC3	ProASIC3 FPGAs qualified for automotive applications
Fusion	Fusion	Mixed signal FPGA integrating ProASIC3 FPGA fabric, programmable analog block, support for ARM [®] Cortex [™] -M1 soft processors, and flash memory into a monolithic device

Note: *The device names link to the appropriate datasheet, including product brief, DC and switching characteristics, and packaging information.

IGLOO Terminology

In documentation, the terms IGLOO series and IGLOO devices refer to all of the IGLOO devices as listed in Table 17-1. Where the information applies to only one product line or limited devices, these exclusions will be explicitly stated.

ProASIC3 Terminology

In documentation, the terms ProASIC3 series and ProASIC3 devices refer to all of the ProASIC3 devices as listed in Table 17-1. Where the information applies to only one product line or limited devices, these exclusions will be explicitly stated.

To further understand the differences between the IGLOO and ProASIC3 devices, refer to the *Industry's Lowest Power FPGAs Portfolio*.

A – Summary of Changes

History of Revision to Chapters

The following table lists chapters that were affected in each revision of this document. Each chapter includes its own change history because it may appear in other device family user's guides. Refer to the individual chapter for a list of specific changes.

Revision (month/year)	Chapter Affected	List of Changes (page number)
Revision 4 (September 2012)	"Microprocessor Programming of Microsemi's Low Power Flash Devices" was revised.	356
Revision 3 (August 2012)	"FPGA Array Architecture in Low Power Flash Devices" was revised.	20
	"Clock Conditioning Circuits in Low Power Flash Devices and Mixed Signal FPGAs" was revised.	129
	"SRAM and FIFO Memories in Microsemi's Low Power Flash Devices" was revised.	173
	"I/O Structures in IGLOO and ProASIC3 Devices" was revised.	210
	"I/O Structures in IGLOOe and ProASIC3E Devices" was revised.	249
	The "Pin Descriptions" and "Packaging" chapters were removed. This information is now published in the datasheet for each product line (SAR 34773).	
	"In-System Programming (ISP) of Microsemi's Low Power Flash Devices Using FlashPro4/3/3X" was revised.	339
	"Boundary Scan in Low Power Flash Devices" was revised.	362
Revision 2 (December 2011)	"Clock Conditioning Circuits in Low Power Flash Devices and Mixed Signal FPGAs" was revised.	129
	"UJTAG Applications in Microsemi's Low Power Flash Devices" was revised.	372
Revision 1 (June 2011)	"Clock Conditioning Circuits in Low Power Flash Devices and Mixed Signal FPGAs" was revised.	129
	"I/O Structures in IGLOO and ProASIC3 Devices" was revised.	210
	"I/O Structures in IGLOOe and ProASIC3E Devices" was revised.	249
	"I/O Software Control in Low Power Flash Devices" was revised.	270
	"In-System Programming (ISP) of Microsemi's Low Power Flash Devices Using FlashPro4/3/3X" was revised.	339
Revision 0 (July 2010)	The ProASIC3L Flash Family FPGAs Handbook was divided into two parts to create the ProASIC3L Low Power Flash FPGAs Datasheet and the ProASIC3L FPGA Fabric User's Guide.	N/A
	"Global Resources in Low Power Flash Devices" was revised.	75
	"Clock Conditioning Circuits in Low Power Flash Devices and Mixed Signal FPGAs" was revised.	129
	"I/O Software Control in Low Power Flash Devices" was revised.	270